

N-Channel 1200V (D-S) SiC MOSFET

Features

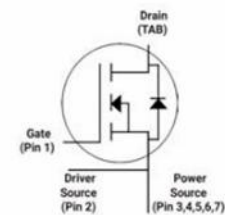
- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Qrr)
- Halogen free, RoHs compliant



TO-263-7

Applications

- Switch mode power supplies
- Renewable energy
- On Board Charger
- High voltage DC/DC converters



Absolute Maximum Ratings ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter		Symbol	Ratings	Unit
Drain Source Voltage		V _{DS}	1200	V
Gate Source Voltage		V _{GS}	-8/+22	V
Recommend Gate Source Voltage		V _{GSop}	-4/+18	V
Drain Current Continuous V _{GS} =18V	T _C =25°C	I _D	65	A
	T _C =125°C		46	
Power Dissipation	T _C =25°C	P _D	326	W
Operating Temperature and Storage Temperature Range		T _J /T _{STG}	-55 to +175	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Case	R_{thJC}	0.46	$^{\circ}\text{C/W}$
Thermal Resistance Junction to Ambient	R_{thJA}	40	$^{\circ}\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =100μA	1200	--	--	V
Gate Leakage Current	I _{GSS}	V _{GS} =18V, V _{DS} =0V	--	--	100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V	--	1	5	μA
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =10mA	2	3	4	V
		V _{DS} =V _{GS} , I _{DS} =10mA, T _J =175°C	--	2.2	--	
Drain-Source On-state Resistance	R _{DS(on)}	V _{GS} =18V, I _D =33A	--	35	45	mΩ
		V _{GS} =18V, I _D =33A, T _J =175°C	--	60	--	
Drain-Source On-state Resistance	R _{DS(on)}	V _{GS} =15V, I _D =33A	--	40	52	mΩ
		V _{GS} =15V, I _D =33A, T _J =175°C	--	70	--	
Total Gate Charge	Q _g	V _{GS(off)} =-4V, V _{GS(on)} =15V V _{DD} =800V, I _D =33A	--	73.3	--	nC
Gate Source Charge	Q _{gs}		--	13.5	--	
Gate Drain Charge	Q _{gd}		--	19	--	
Turn-On Switching Energy	E _{ON}	V _{GS} =-4/+15V, V _{DD} =800V · I _D =20A, R _G =3.8Ω, L=120uH	--	0.29	--	mJ
Turn-Off Switching Energy	E _{OFF}		--	0.08	--	
Turn-on Delay Time	t _{d(on)}		--	26.8	--	ns
Turn-on Rise Time	t _r		--	25	--	
Turn-off Delay Time	t _{d(off)}		--	29.6	--	
Turn-off Fall Time	t _f		--	12.8	--	
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =1000V, V _{AC} =25mV, f=1MHz	--	2735	--	pF
Output Capacitance	C _{oss}		--	101	--	
Reverse Transfer Capacitance	C _{rss}		--	7.5	--	
Gate resistance	R _G	V _{AC} = 25mV, f=1MHz	--	2.4	--	Ω

Reverse Diode Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Diode Forward Voltage	V _{SD}	I _{SD} =20A, V _{GS} =-4V	--	4.2	--	V
		I _{SD} =20A, V _{GS} =-4V, T _J =175°C	--	3.8	--	
Continuous Diode Forward Current	I _{SD}	V _{GS} =-4V	--	65	--	A
Reverse Recovery Time	t _{rr}	V _R =800V, I _F =33A, V _{GS} =-4V, di/dt=1011A/μs	--	18.8	--	ns
Reverse Recovery Charge	Q _{rr}		--	120.4	--	nC
Reverse Recovery Energy	E _{REC}		--	0.9	--	uJ
Peak Reverse Recovery Current	I _{rrm}		--	11	--	A
Charge Time	t _A		--	10	--	ns
DisCharge Time	t _B		--	8.8	--	ns
Reverse Recovery Time	t _{rr}	V _R =800V, I _F =33A, V _{GS} =-4V, di/dt=1011A/μs T _J =175°C	--	53	--	ns
Reverse Recovery Charge	Q _{rr}		--	662	--	nC
Reverse Recovery Energy	E _{REC}		--	161	--	μJ
Peak Reverse Recovery Current	I _{rrm}		--	19	--	A
Charge Time	t _A		--	16.4	--	ns
DisCharge Time	t _B		--	33.8	--	ns

Typical Characteristics Curves ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Figure 1. Output Characteristic ($T_J = -55^\circ\text{C}$)

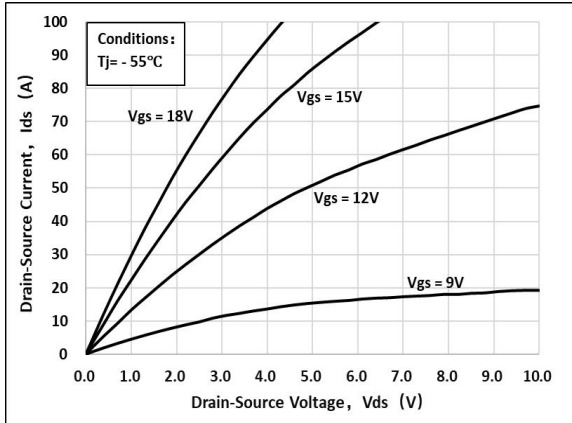


Figure 2. Output Characteristic ($T_J = 25^\circ\text{C}$)

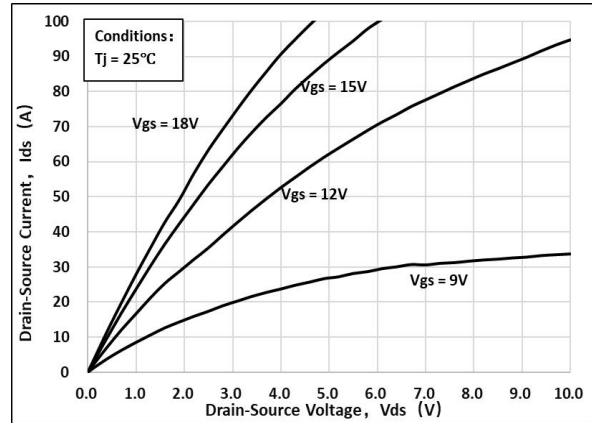


Figure 3. Output Characteristic ($T_J = 175^\circ\text{C}$)

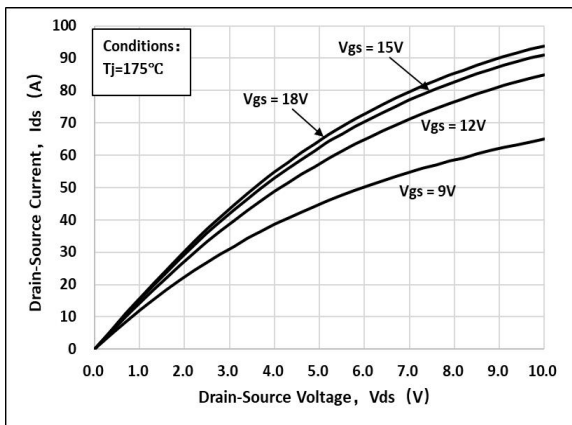


Figure 4. $R_{DS(on)}$ Vs I_{DS} Characteristic

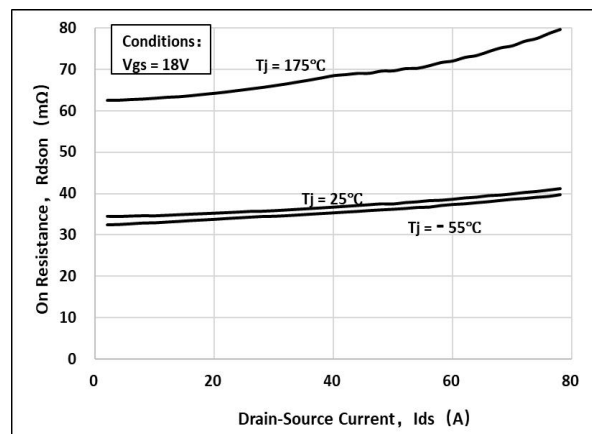


Figure 5. $R_{DS(on)}$ vs. Temperature

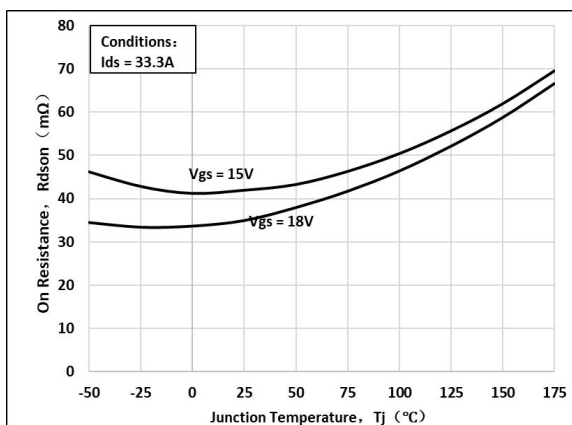
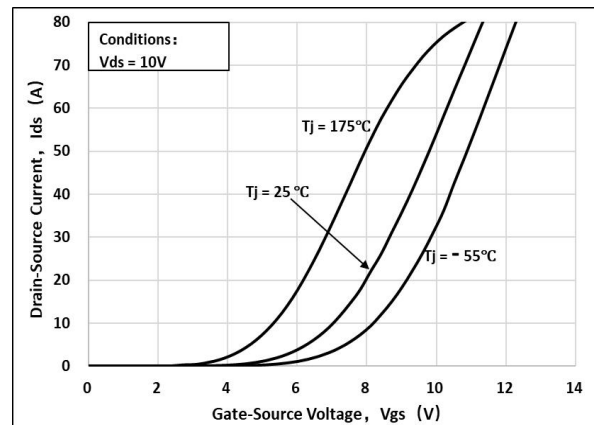


Figure 6. Transfer Characteristic



Typical Characteristics Curves ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Figure 7: Body-diode Characteristic ($T_J = -55^\circ\text{C}$)

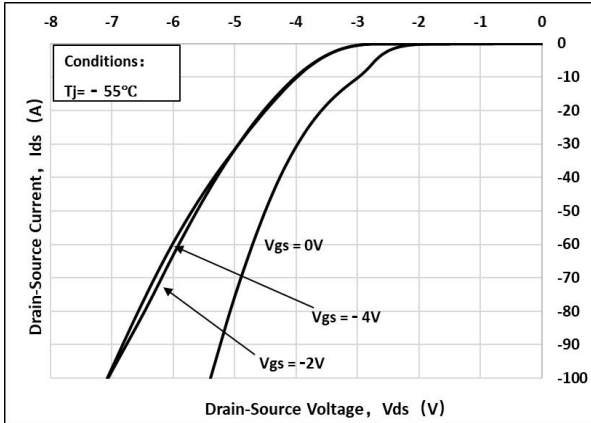


Figure 8: Body-diode Characteristic ($T_J = 25^\circ\text{C}$)

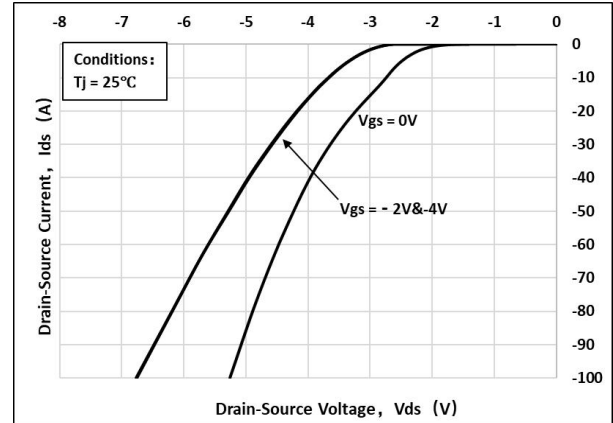


Figure 9: Body-diode Characteristic ($T_J = 175^\circ\text{C}$)

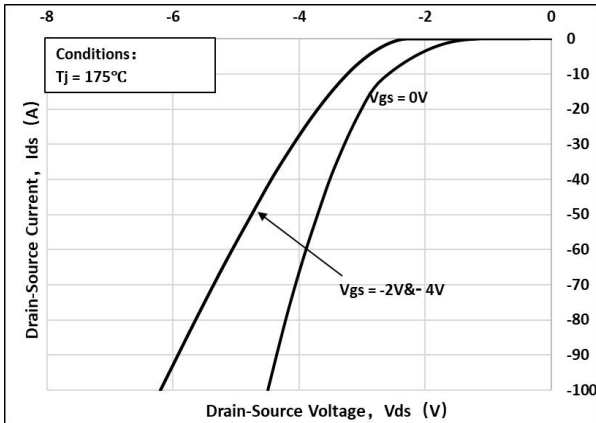


Figure 10: V_{TH} Vs T_J Temperature Characteristic

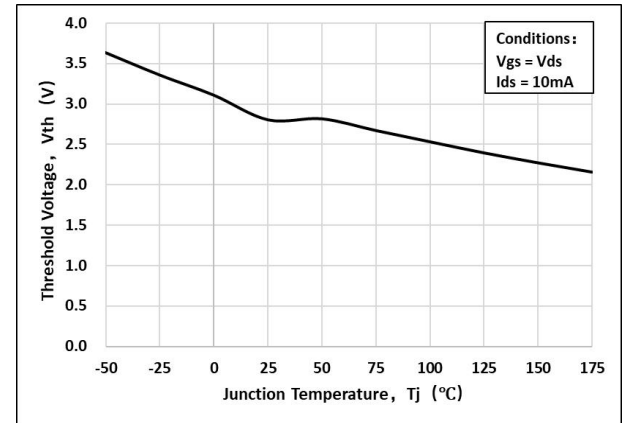


Figure 11: 3rd Quadrant Characteristic ($T_J = -55^\circ\text{C}$)

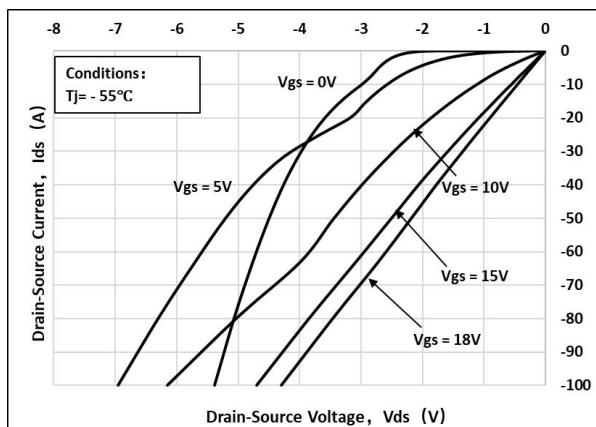
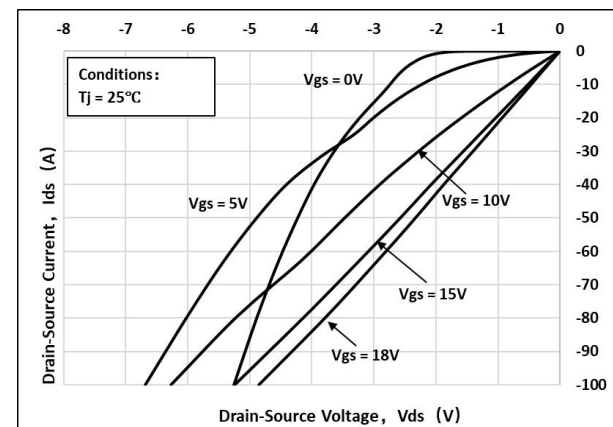


Figure 12: 3rd Quadrant Characteristic ($T_J = 25^\circ\text{C}$)



Typical Characteristics Curves ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Figure 13: 3rd Quadrant Characteristic ($T_J = 175^\circ\text{C}$)

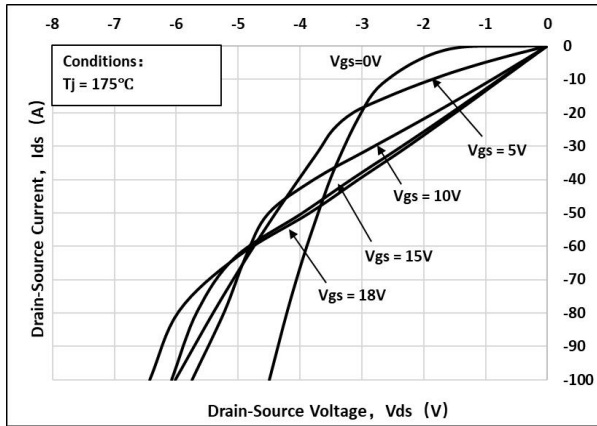


Figure 14: Gate Charge Characteristics

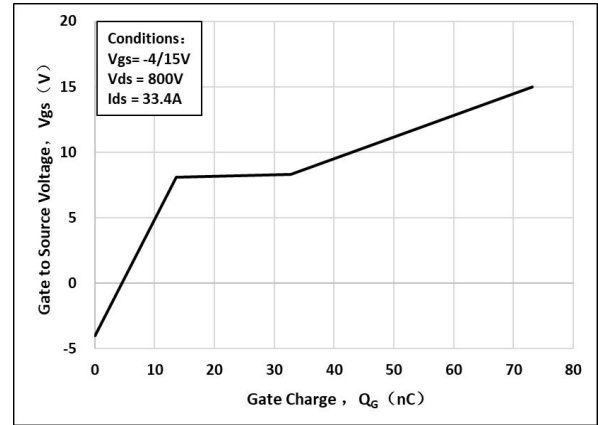


Figure 15: Drain Current vs. Case Temperature

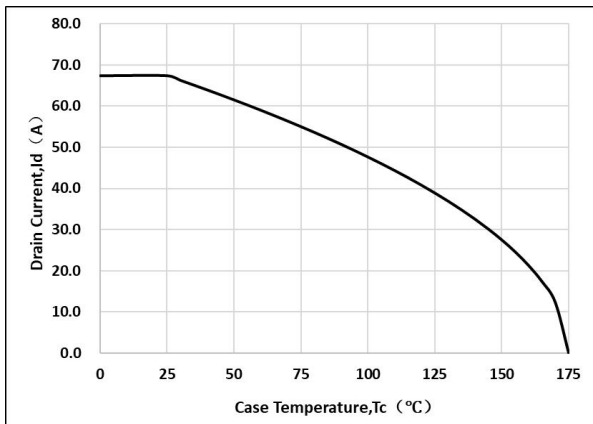


Figure 16: Safe Operating Area

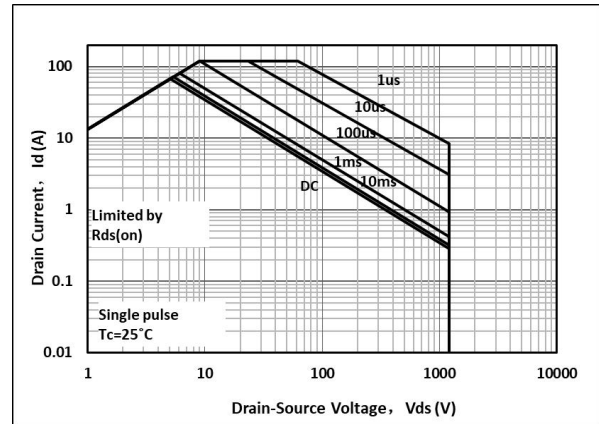


Figure 17: Capacitance Characteristics

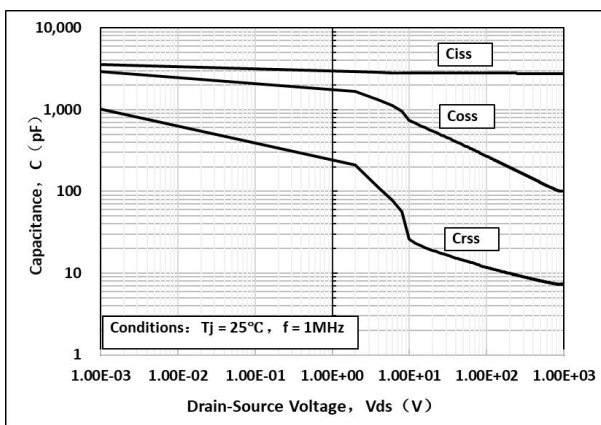
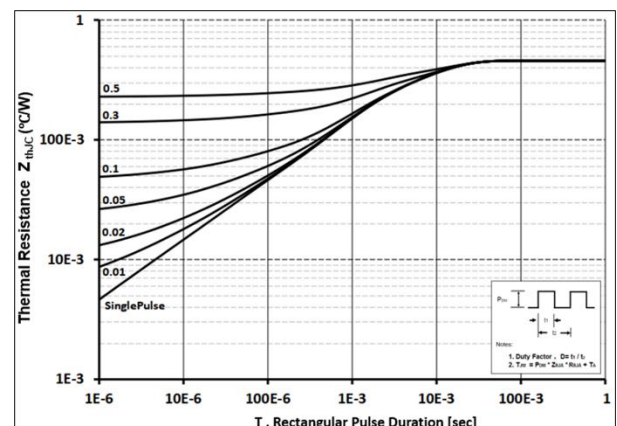


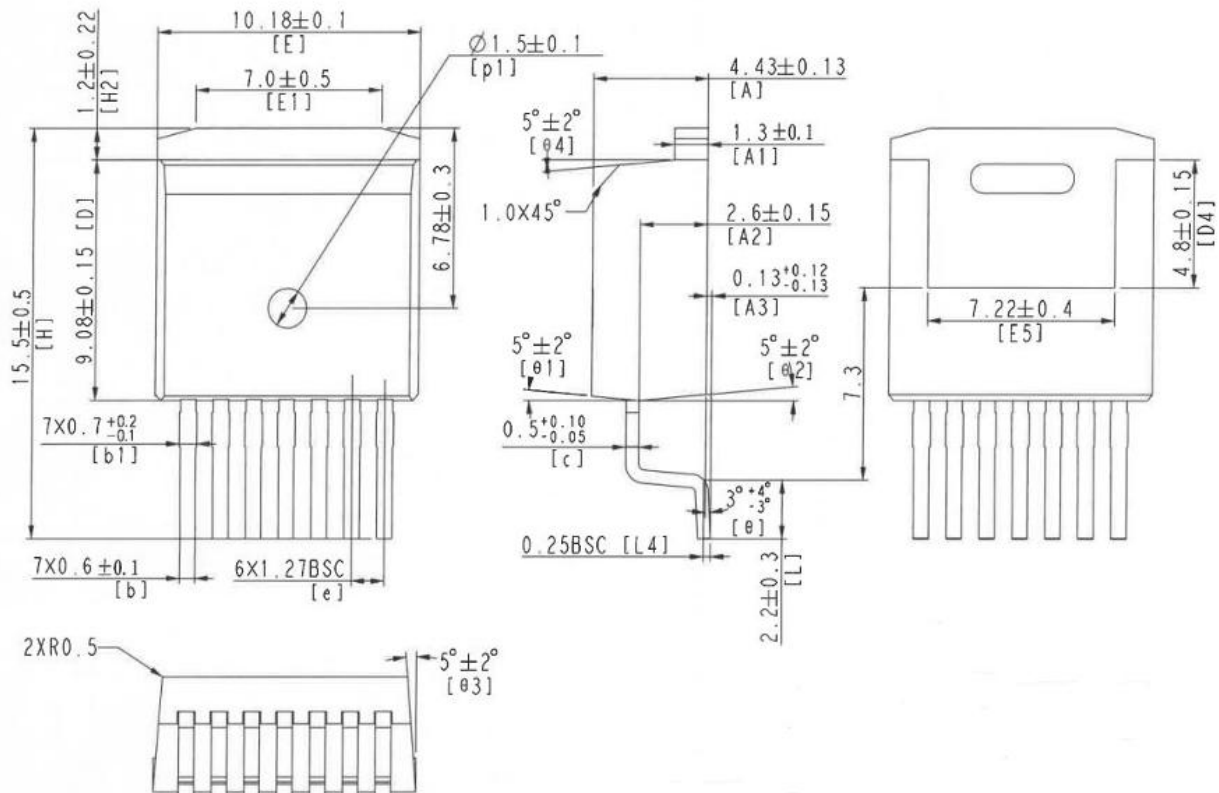
Figure 18: Transient Thermal Impedance



Package Outline Dimensions (Unit: millimeters)

TO-263-7

UNIT:mm



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